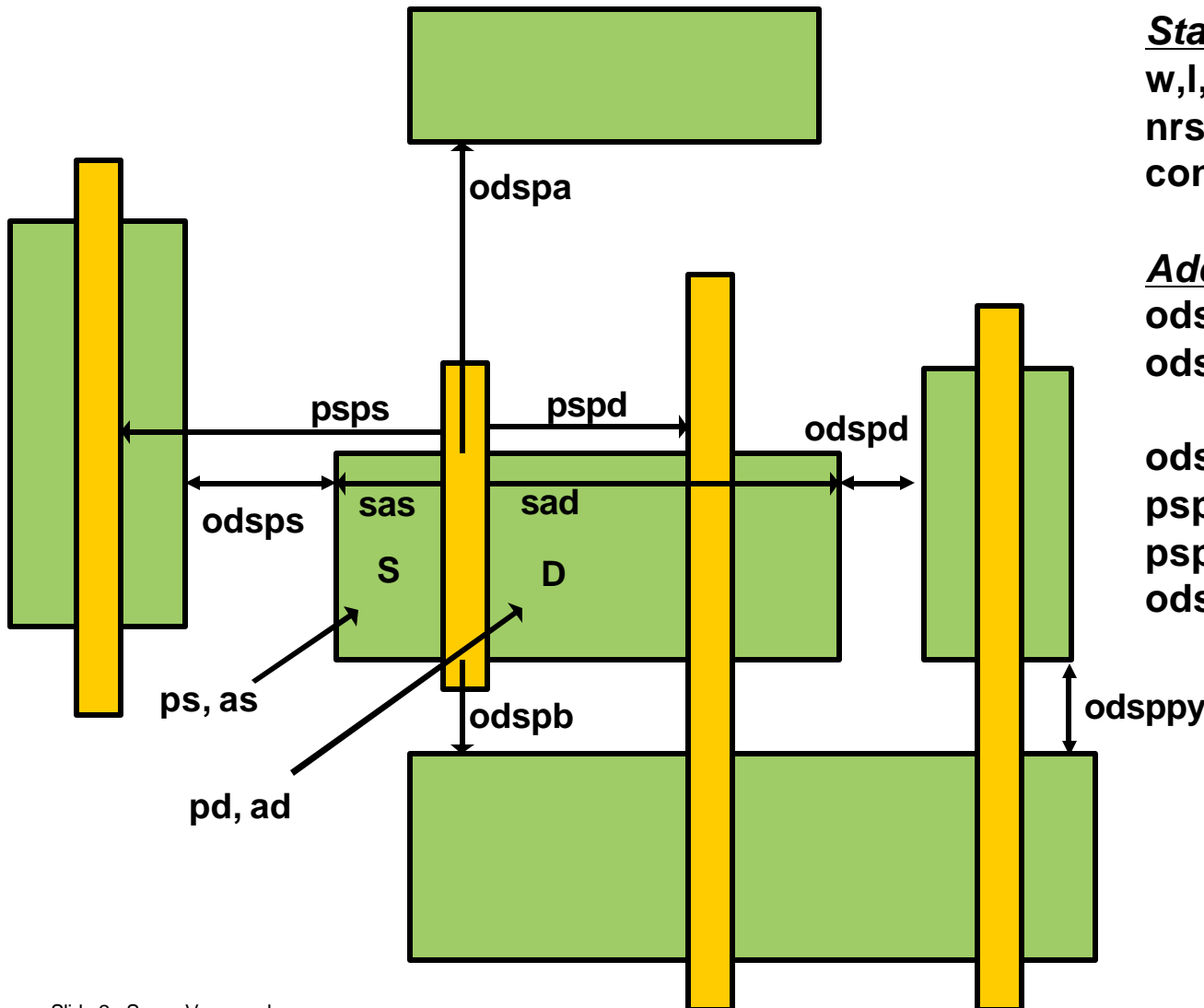


# FET Parasitic Extraction

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# MOSFET Geometric Parameters for LPE



## Standard parameters

w,l,ad,as,pd,ps

nrs,nrd: effective R from contact to edge of gate

## Additional parameters

odspa, odspb: effective W

odspa,odspb: parasitic device leakages

odspas,odspd: active stress

psps, pspd: effective L

psps, pspd: implant shadow

odspys: dopant interdiffusion

